

AMENDMENTS TO THE CLAIMS

1-16. (Canceled)

17. (Previously presented) A solid state imaging element comprising:

a plurality of pixels arranged in a matrix, each of which has a photoelectric conversion element, a transfer switch for transferring charge stored in said photoelectric conversion element, a charge store part for storing charge transferred by said transfer switch, a reset switch for resetting said charge store part, and an amplifying element for outputting a signal in accordance with a potential of said charge stored in said charge store part;

wherein a threshold voltage of said amplifying element is reduced in relation to remaining transistors of each pixel, and further wherein a diffusion region that is connected to a power source is laid out to be physically adjacent to the photoelectric conversion element in order to provide an overflow path,

wherein said transfer switch is an enhancement type transistor.

18-23. (Canceled)

24. (Previously presented) A solid state imaging element comprising:

a transfer switch having a source being a floating diffusion and a drain being a photodiode;

a reset switch having a source being said floating diffusion and a drain being electrically connected to a vertical selection line, said reset switch being a depression type transistor.

25. (Previously presented) A solid-state imaging element as claimed in claim 24, wherein a matrix has a row (n) of pixels and a row (n+1) of pixels, each unit pixel (n, m) in said row (n) of pixels including said transfer switch and said reset switch.

26. (Previously presented) A solid-state imaging element as claimed in claim 25, wherein each unit pixel (n+1, m) in said row (n+1) includes another transfer switch and another reset switch, said another reset switch having a drain electrically connected to another vertical selection line.

27. (Previously presented) A solid-state imaging element as claimed in claim 25, wherein said row (n) is selected while said row (n+1) is non-selected, said row (n+1) being selected while said row (n) is non-selected.

28. (Previously presented) A solid-state imaging element as claimed in claim 24, further comprising:

an amplifying switch having a gate electrically connected to said floating diffusion, a source electrically connected to a vertical signal line, and a drain electrically connected to a power source line.

29. (Previously presented) A solid-state imaging element as claimed in claim 28, wherein said amplifying switch is an enhancement type transistor.

30. (Previously presented) A solid-state imaging element as claimed in claim 24, wherein said transfer switch is an enhancement type transistor.

31. (Canceled)

32. (Previously presented) A solid-state imaging element as claimed in claim 24, wherein said reset switch has a gate electrically connected to a reset line.

33. (Previously presented) A solid-state imaging element as claimed in claim 24, wherein said photodiode is configured to photoelectrically convert incident light into a signal charge.

34. (New) A solid-state imaging element as claimed in claim 24, wherein a gate of said transfer switch is electrically connected to a source of a transfer selection switch, a gate of said transfer selection switch being electrically connected to said vertical selection line.

35. (New) A solid-state imaging element as claimed in claim 34, wherein a drain of said transfer selection switch is electrically connected to a transfer line.

36. (New) A solid-state imaging element as claimed in claim 34, wherein said transfer selection switch is an enhancement type transistor.